Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	519	427/237.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/29 11:12
L2	692	427/578.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON .	2006/06/29 11:12
L3	19069	(chamber or reactor) with wall with (coat\$3 or layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/29 11:17
L4	15	2 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/29 11:14
L5	154	(chamber or reactor) with wall with (coat\$3 or layer) and clean same (chlor\$3 or "cl.sub."\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/29 11:21
L6	1664638	5 and silicon or si	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/29 11:20
L7	94	5 and (silicon or si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/29 11:21
L8	328	(chamber or reactor) with wall with (coat\$3 or layer) and clean\$3 same (chlor\$3 or "cl.sub."\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/29 11:21
L9	198	8 and (silicon or si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/29 11:21

S1	2	"6479098".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 10:25
S2	27	seasoning layer same (silicon dioxide or silicon oxide or sio2 or "sio.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 10:29
<b>S</b> 3	1	S2 and chlorine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 10:28
S4	1	S2 and (chlorine or cl)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 10:29
<b>S</b> 5	41	seasoning layer and (silicon dioxide or silicon oxide or sio2 or "sio.sub. 2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 10:39
S6	6	S5 and (chlorine or cl)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 10:35
S8	6	S5 and (chlorine or cl or "CCl.sub.4" or "C.sub.2" "Cl.sub.6")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 10:37
S9	6	seasoning layer and (chlorine or cl or "CCI.sub.4" or "C.sub.2" "Cl.sub. 6")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 10:37
S10	38	S5 and (clean\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 11:37
S11	248122	(reactor or chamber) same (treat\$4 or pretreat\$4 or coat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 11:38

S12	4960	(reactor or chamber) same (treat\$4 or pretreat\$4 or coat\$3) same (silicon dioxide or silicon oxide or sio2 or "sio.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 12:04
S13	2163	S12 and (clean\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 11:39
S14	124	S12 and (clean\$3) same (chlorine or cl or "CCl.sub.4" or "C.sub.2" "Cl. sub.6")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 12:05
S15	7367	(reactor or chamber) same (treat\$4 or pretreat\$4 or coat\$3 or condition\$3) same (silicon dioxide or silicon oxide or sio2 or "sio.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 12:04
S16	337	S15 and (clean\$3) same (chlorine or cl or "cl.sub.2" or "CCl.sub.4" or "C. sub.2Cl.sub.6")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 14:34
S17	213	S16 not S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 12:06
S18	138	S17 and (silane or "sih.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 14:32
S19	101	(chamber or reactor) same (silicon dioxide or silicon oxide or sio2 or "sio.sub.2") same flak\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 14:35
S20	7	S19 and (clean\$3) same (chlorine or cl or "cl.sub.2" or "CCl.sub.4" or "C. sub.2Cl.sub.6")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 14:35
S21	1006	(chamber or reactor) same flak\$3 and (silicon dioxide or silicon oxide or sio2 or "sio.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 16:12

S22	156	S21 and (clean\$3) same (chlorine or cl or "cl.sub.2" or "CCl.sub.4" or "C. sub.2Cl.sub.6")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 15:33
S23	765	dichlorosilane with (ammonia or "nh.sub.3") same pressure same silicon nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 15:36
S24	0	dichlorosilane with (ammonia or "nh.sub.3") same pressure same silicon nitride and season\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 15:36
S25	177	dichlorosilane with (ammonia or "nh.sub.3") same pressure with torr same silicon nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 15:45
S26	15	season\$3 same silicon oxide same silicon nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 15:48
S27	1	season\$3 same silicon oxide same silicon nitride same silicon carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 15:56
S28	5	season\$3 same silicon nitride same silicon carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 15:58
S29	19	season\$3 same silicon carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 16:10
S30	50	season\$3 same (silicon carbide or sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 16:00
S31	31	S30 not S29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 16:00

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S32	453	season\$3 and silicon carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 16:10
S33	69	season\$3 same (chamber or reactor) and silicon carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/20 16:11
S34	19048	(chamber or reactor) with wall with (coat\$3 or layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/29 11:14
S35	1362	(chamber or reactor) with wall with (coat\$3 or layer) same (silicon or si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 16:13
S36	443	(chamber or reactor) wall with (coat\$3 or layer) same (silicon or si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 16:17
S37	56	(chamber or reactor) with wall with (coat\$3 or layer) same amorphous (silicon or si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 16:29
S38	250	(chamber or reactor) with wall with (coat\$3 or layer) and amorphous (silicon or si) and silicon nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 16:30
S39	230	S38 not S37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 16:38
540	70	S39 and (chlorine or "cl.sub."\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 16:39
S41	14	(chamber or reactor) with wall with (coat\$3 or layer) same silicon nitride and amorphous silicon same plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 16:54

S42	2	"5,904,778".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT;	ADJ	ON	2006/06/28 16:52
S43	14	(chamber or reactor) with wall with	IBM_TDB US-PGPUB;	ADJ	ON	2006/06/28 16:56
		(coat\$3 or layer or season\$3 or condition\$3) same silicon nitride and amorphous silicon same plasma	USPAT; EPO; JPO; DERWENT; IBM_TDB			
S44	15	(chamber or reactor) with wall with (coat\$3 or layer or season\$3 or condition\$3) same silicon (oxide or carbide or nitride) and amorphous silicon same plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 17:00
S45	1	S44 not S41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 16:56
S46	30	(chamber or reactor) with wall same (coat\$3 or layer or season\$3 or condition\$3) same silicon (oxide or carbide or nitride) and amorphous silicon same plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/29 10:08
S47	15	S46 not S44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/28 17:00